

SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

EMH2407R — General-Purpose Switching Device Applications

Features

- ON-resistance RDS(on)1 : $16m\Omega(typ.)$
- · Common-drain type
- · Halogen free compliance

- · Best suited for LiB charging and discharging switch
- · 2.5V drive

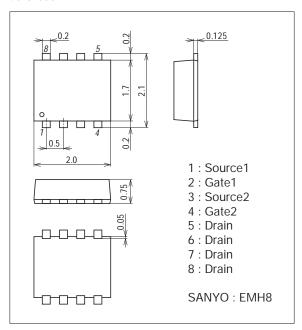
Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		20	V
Gate-to-Source Voltage	VGSS		±12	V
Drain Current (DC)	ID		6	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	60	Α
Allowable Power Dissipation	PD	When mounted on ceramic substrate (900mm ² x0.8mm) 1unit	1.3	W
Total Dissipation	PT	When mounted on ceramic substrate (900mm ² ×0.8mm)	1.4	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Package Dimensions

unit : mm (typ) 7045-006



Product & Package Information

• Package : EMH8

• JEITA, JEDEC :-

• Minimum Packing Quantity : 3,000 pcs./reel

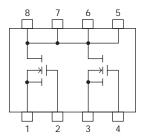
Taping Type: TL



Marking



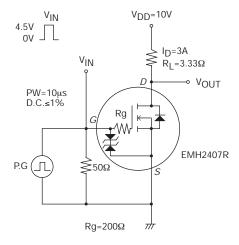
Electrical Connection

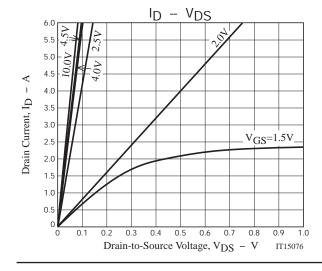


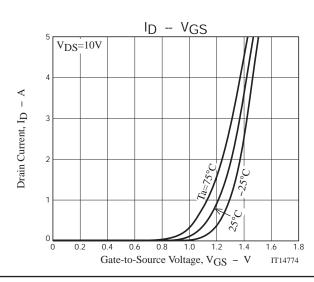
Electrical Characteristics at Ta=25°C

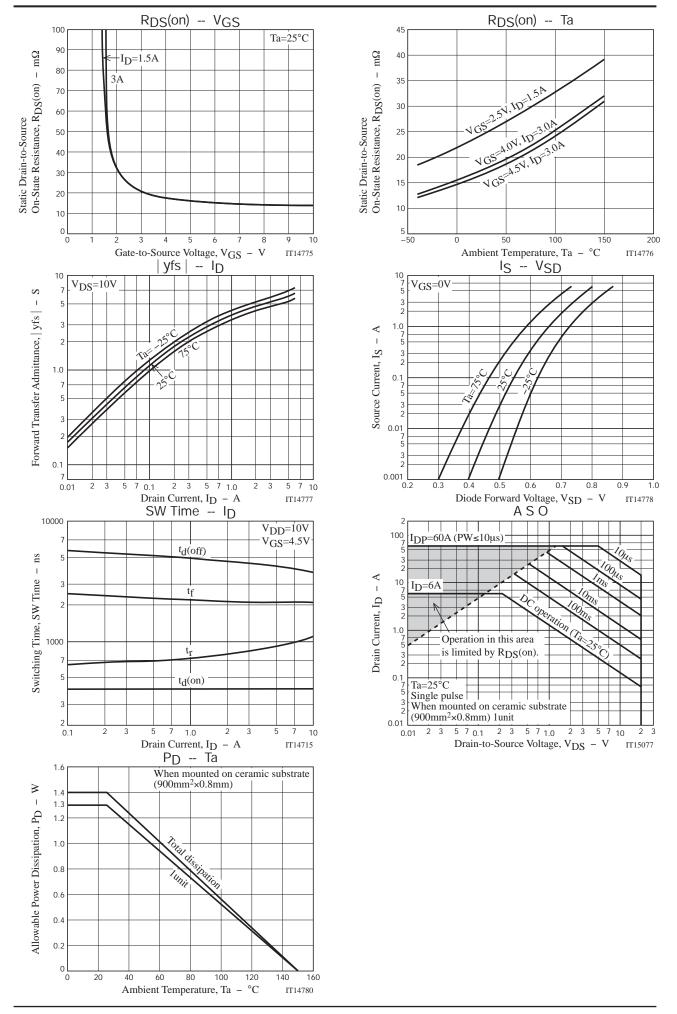
Parameter	Symbol	Conditions	Ratings			Linit
Parameter			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	20			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =20V, V _{GS} =0V			-1	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0V			±10	μΑ
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	0.5		1.3	٧
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =3A		5		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	I _D =3A, V _{GS} =4.5V	11	16	21	$m\Omega$
	R _{DS} (on)2	I _D =3A, V _{GS} =4V	11.5	17	23	$m\Omega$
	R _{DS} (on)3	I _D =1.5A, V _{GS} =2.5V	14	24	34	mΩ
Turn-ON Delay Time	t _d (on)	See specified Test Circuit.		400		ns
Rise Time	t _r	See specified Test Circuit.		820		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		4500		ns
Fall Time	tf	See specified Test Circuit.		2100		ns
Total Gate Charge	Qg	V _D S=10V, V _G S=4.5V, I _D =6A		60		nC
Gate-to-Source Charge	Qgs	V _D S=10V, V _G S=4.5V, I _D =6A		14		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =10V, V _{GS} =4.5V, I _D =6A		13		nC
Diode Forward Voltage	V _{SD}	IS=6A, VGS=0V		0.8	1.2	V

Switching Time Test Circuit









Note on usage: Since the EMH2407R is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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